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FGH40T65UPD 650 V, 40 A Field Stop Trench IGBT

Features

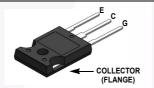
- Maximum Junction Temperature : T_J = 175°C
- · Positive Temperaure Co-efficient for Easy Parallel Operating
- · High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.65 V(Typ.) @ I_C = 40 A
- 100% of Parts Tested I_{LM(2)}
- · High Input Impedance
- Tightened Parameter Distribution
- RoHS Compliant
- Short Circuit Ruggedness > 5 us @25°C

General Description

Using innovative field stop trench IGBT technology, Fairchild's new series of field-stop trench IGBTs offer optimum performance for solar inverter, UPS, welder, and digital power generator where low conduction and switching losses are essential.

Applications

- · Solar Inverter, UPS, Welder, Digital Power Generator
- · Telecom, ESS





Absolute Maximum Ratings

| Symbol | Description | | Ratings | Unit | |
|---------------------|---|--------------------------|-------------|------|--|
| V _{CES} | Collector to Emitter Voltage | | 650 | V | |
| V _{GES} | Gate to Emitter Voltage | | ± 20 | V | |
| GES | Transient Gate to Emitter Voltage | | ± 25 | V | |
| I _C | Collector Current | @ T _C = 25°C | 80 | A | |
| ic | Collector Current | @ T _C = 100°C | 40 | A | |
| I _{CM (1)} | Pulsed Collector Current | | 120 | А | |
| I _{LM (2)} | Clamped Inductive Load Current | @ T _C = 25°C | 120 | А | |
| l _F | Diode Forward Current | @ T _C = 25°C | 40 | A | |
| | Diode Forward Current | @ T _C = 100°C | 20 | A | |
| I _{FM(1)} | Pulsed Diode Maximum Forward Current | | 120 | Α | |
| P _D | Maximum Power Dissipation | @ T _C = 25°C | 268 | W | |
| | Maximum Power Dissipation | @ T _C = 100°C | 134 | W | |
| SCWT | Short Circuit Withstand Time @ T _C = 25°C | | 5 | us | |
| T _J | Operating Junction Temperature | | -55 to +175 | °C | |
| T _{stg} | Storage Temperature Range | | -55 to +175 | °C | |
| T _L | Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds | | 300 | °C | |

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

2: Ic = 120 A, Vce = 400 V, Rg = 15 Ω

Thermal Characteristics

| Symbol | Parameter | Тур. | Max. | Unit |
|------------------------|---|------|------|------|
| $R_{\theta JC}(IGBT)$ | Thermal Resistance, Junction to Case | - | 0.56 | °C/W |
| $R_{\theta JC}(Diode)$ | Thermal Resistance, Junction to Case | - | 1.71 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | | 40 | °C/W |

Package Marking and Ordering Information

| Part Number | Part Number Top Mark | | Packing Method | Reel Size | Reel Size Tape Width | Quantity | |
|-------------|----------------------|------------|-------------------|-----------|----------------------|----------|--|
| FGH40T65UPD | FGH40T65UPD | TO-247 A03 | Tube | N/A | N/A | 30 | |

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|------------------------------------|--|--|------|------|------|------|
| Off Charac | eteristics | | | | | |
| BV _{CES} | Collector to Emitter Breakdown Voltage | V _{GE} = 0 V, I _C = 1 mA | 650 | - | - | V |
| $\frac{\Delta BV_CES}{\Delta T_J}$ | Temperature Coefficient of Breakdown Voltage | V _{GE} = 0 V, I _C = 250 uA | - | 0.65 | - | V/°C |
| I _{CES} | Collector Cut-Off Current | $V_{CE} = V_{CES}, V_{GE} = 0 V$ | /- | - | 250 | μΑ |
| I _{GES} | G-E Leakage Current | $V_{GE} = V_{GES}, V_{CE} = 0 V$ | - | - | ±400 | nA |
| On Charac | eteristics | | | | | |
| V _{GE(th)} | G-E Threshold Voltage | I _C = 40 mA, V _{CE} = V _{GE} | 4.0 | 6.0 | 7.5 | V |
| OL(III) | | I _C = 40 A, V _{GE} = 15 V | - | 1.65 | 2.3 | V |
| V _{CE(sat)} | Collector to Emitter Saturation Voltage | I _C = 40 A, V _{GE} = 15 V, T _C = 175°C | - | 2.1 | - | V |
| Dynamic C | Characteristics | | | | | |
| C _{ies} | Input Capacitance | | - | 2730 | 3630 | pF |
| C _{oes} | Output Capacitance | $V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz | - | 82 | 110 | pF |
| C _{res} | Reverse Transfer Capacitance | - I = I IVIDZ | - | 48 | 72 | pF |
| Switching | Characteristics | | • | | | |
| t _{d(on)} | Turn-On Delay Time | V _{CC} = 400 V, I _C = 40 A, | - | 20 | 26 | ns |
| t _r | Rise Time | | - | 26 | 34 | ns |
| t _{d(off)} | Turn-Off Delay Time | | - | 144 | 187 | ns |
| t _f | Fall Time | R_G = 7 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C | - | 17 | 22 | ns |
| E _{on} | Turn-On Switching Loss | maddive Lodd, 16 20 0 | - | 1.59 | 2.1 | mJ |
| E _{off} | Turn-Off Switching Loss | | - | 0.58 | 0.76 | mJ |
| E _{ts} | Total Switching Loss | | - | 2.17 | 2.86 | mJ |
| t _{d(on)} | Turn-On Delay Time | | - | 19 | - | ns |
| t _r | Rise Time | | - | 38 | - | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$ | - | 153 | - / | ns |
| t _f | Fall Time | $R_G = 7 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 175^{\circ}C$ | - | 60 | - | ns |
| E _{on} | Turn-On Switching Loss | | - | 1.84 | - \ | mJ |
| E _{off} | Turn-Off Switching Loss | | - | 0.98 | - | mJ |
| E _{ts} | Total Switching Loss | | - | 2.82 | - | mJ |
| T _{SC} | Short Circuit Withstand Time | V_{GE} = 15 V, V_{CC} =400 V, R_{G} = 10 Ω | 5 | - | - | us |
| Q _g | Total Gate Charge | | - | 177 | 265 | nC |
| Q _{ge} | Gate to Emitter Charge | V _{CE} = 400 V, I _C = 40 A, V _{GE} = 15 V | - | 23 | 35 | nC |
| Q _{gc} | Gate to Collector Charge | GE - 10 V | - | 100 | 150 | nC |

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | | Min. | Тур. | Max | Unit |
|------------------------|------------------------------------|---|------------------------|------|------|-----|------|
| V _{FM} | Diode Forward Voltage | I _F = 20 A | T _C = 25°C | - | 2.1 | 2.7 | V |
| V FM | 2.040 : 0.114.4 : 0.1490 | | T _C = 175°C | - | 1.9 | - | |
| E _{rec} | Reverse Recovery Energy | | T _C = 175°C | - | 96 | - | uJ |
| t | Diode Reverse Recovery Time | I _F = 20 A, di _F /dt = 200 A/μs | T _C = 25°C | - | 33 | 43 | ns |
| Diode Reverse Recovery | 2.000 1.010.00 1.00010.9 1 | ης – 20 Λ, αιριαι – 200 Λιμο | T _C = 175°C | - | 128 | - | |
| Q _{rr} | Diode Reverse Recovery Charge | | T _C = 25°C | - | 53 | 74 | nC |
| ~11 | 2.535 No. 5. 5. 1000 Tolly Ollargo | | T _C = 175°C | - | 341 | - | 0 |

Figure 1. Typical Output Characteristics

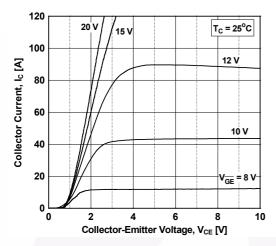


Figure 3. Typical Saturation Voltage Characteristics

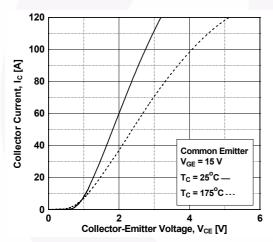


Figure 5. Saturation Voltage vs. V_{GE}

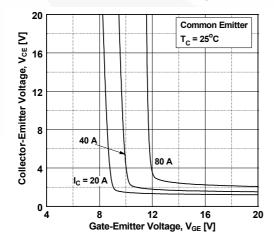


Figure 2. Typical Output Characteristics

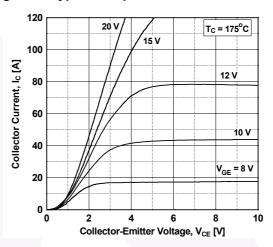


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

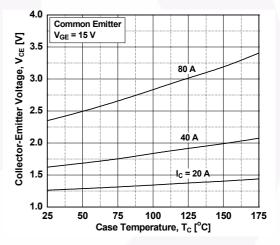


Figure 6. Saturation Voltage vs. V_{GE}

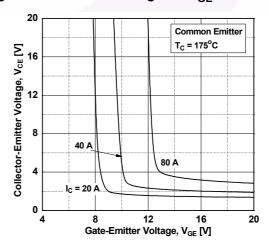


Figure 7. Capacitance Characteristics

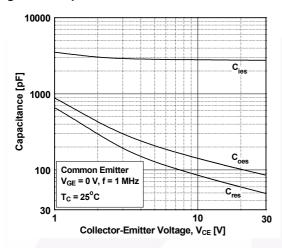


Figure 9. Turn-on Characteristics vs.
Gate Resistance

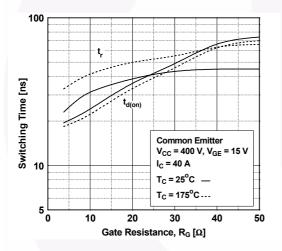


Figure 11. Switching Loss vs.

Gate Resistance

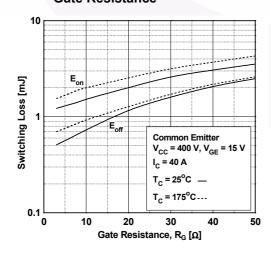


Figure 8. Gate charge Characteristics

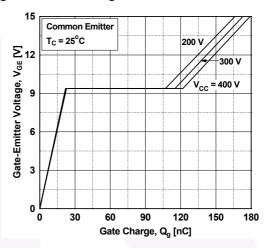


Figure 10. Turn-off Characteristics vs. Gate Resistance

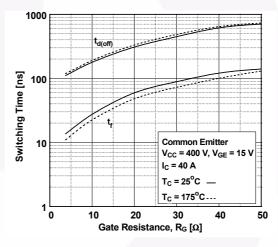


Figure 12. Turn-on Characteristics vs. Collector Current

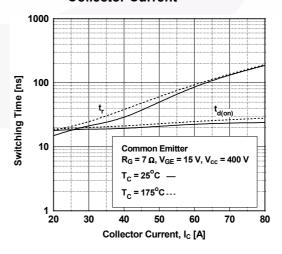


Figure 13. Turn-off Characteristics vs. Collector Current

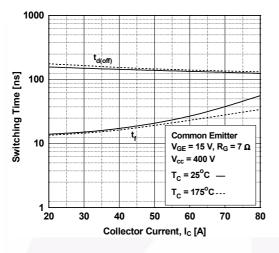


Figure 14. Switching Loss vs. Collector Current

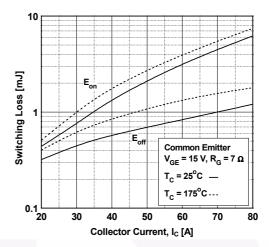


Figure 15. Load Current vs. Frequency

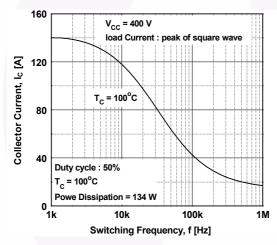


Figure 16. SOA Characteristics

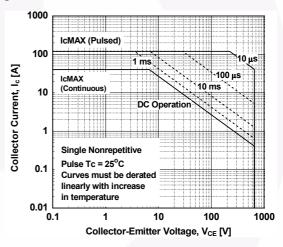


Figure 17. Forward Characteristics

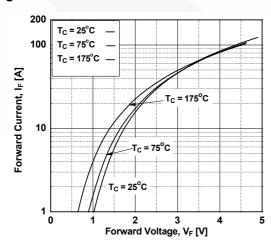


Figure 18. Reverse Revovery Current

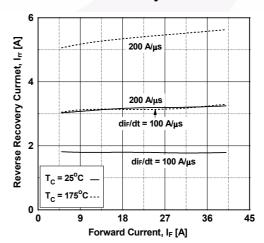


Figure 19. Reverse Recovery Time

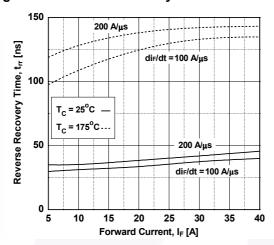


Figure 20. Stored Charge

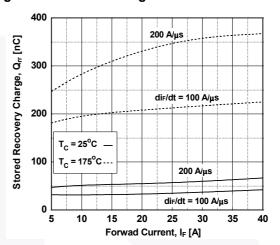


Figure 21. Transient Thermal Impedance of IGBT

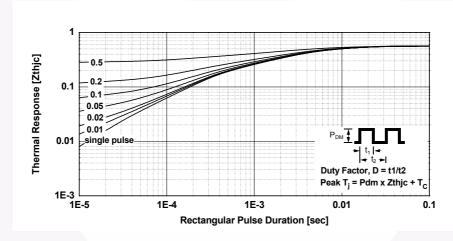
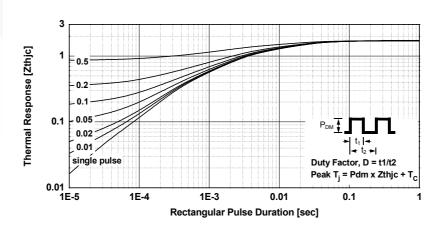
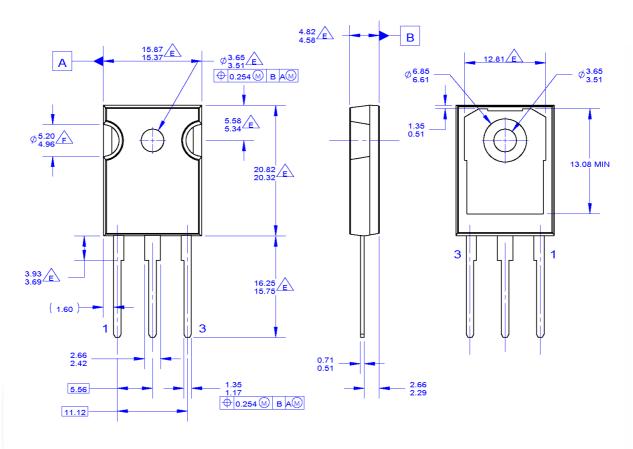


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247,
- ISSUE E, VARIATION AB, DATED JUNE, 2004. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
 ALL DIMENSIONS ARE IN MILLIMETERS
- D. DRAWING CONFORMS TO ASME Y14.5 1994
- E DOES NOT COMPLY JEDEC STANDARD VALUE
- NOTCH MAY BE SQUARE DRAWING FILENAME: MKT-TO247A03_REV03

Figure 23. TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB (Active)

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Dimensions in Millimeters





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|--------------------------|-----------------------|---|
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